TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (DARLINGTON)

2 S D 2 6 0 4

HIGH POWER SWITCHING APPLICATIONS

HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS

• High DC Current Gain : hFE=2000 (Min.)

• Low Saturation Voltage: VCE (sat)=1.5V (Max.)

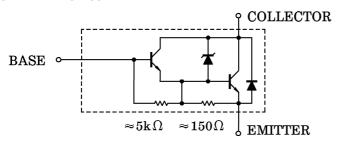
MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage		v_{CBO}	95	V	
Collector-Emitter Voltage		v_{CEO}	110±15	V	
Emitter-Base Voltage		$v_{ m EBO}$	5	V	
Collector Current	DC	$I_{\mathbf{C}}$	5	A	
	Pulse	I_{CP}	10	A	
Base Current		$I_{\mathbf{B}}$	0.7	A	
Collector Power	$Ta = 25^{\circ}C$	$P_{\mathbf{C}}$	2.0	w	
Dissipation	$Tc = 25^{\circ}C$	10	20		
Junction Temperature		T_{j}	150	°C	
Storage Temperature Range		$\mathrm{T_{stg}}$	-55~150	°C	

Unit in mm 10±0.3 0.75±0.15 1.1 1.1 1.1 0.75±0.15 2.54±0.25 1. BASE 2. COLLECTOR 3. EMITTER JEDEC JEITA SC-67 TOSHIBA 2-10R1A

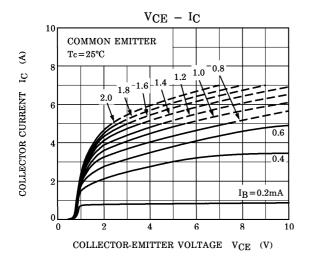
Weight: 1.7 g (Typ.)

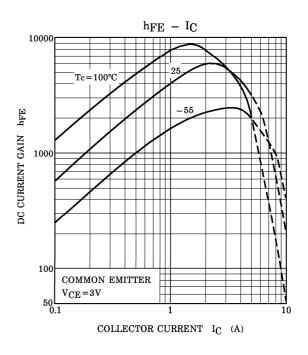
EQUIVALENT CIRCUIT

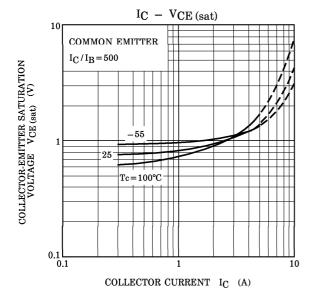


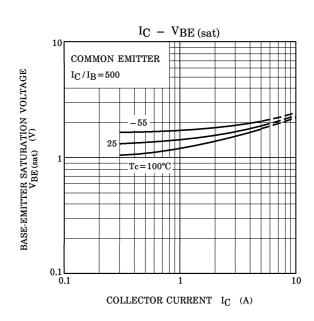
ELECTRICAL CHARACTERISTICS (Tc = 25°C)

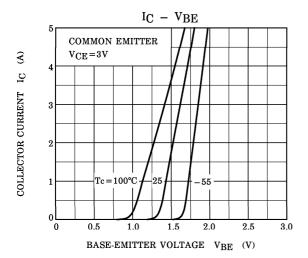
CHARA	CTERISTIC	SYMBOL	TEST CONDITION		TYP.	MAX.	UNIT	
Collector Cut-off Current I		I_{CBO}	$V_{CB} = 90V, I_{E} = 0$	_	_	100	μ A	
Emitter Cut-off Current		$I_{ m EBO}$	$V_{EB}=6V, I_{C}=0$	0.75	_	3.0	μ A	
Collector-Emitter Breakdown Voltage		V (BR) CEO	$I_{C}=10mA, I_{B}=0$	95	110	125	V	
DC Current Gain		h _{FE} (1)	$V_{CE}=3V$, $I_{C}=2A$	2000	_	15000		
		h _{FE} (2)	$V_{CE}=3V$, $I_{C}=5A$	1000	_	_		
Collector-Emitter Saturation Voltage		V _{CE} (sat)	$I_C=2A$, $I_B=4mA$	_	0.9	1.5	V	
Base-Emitter Saturation Voltage		V _{BE} (sat)	$I_C=2A$, $I_B=4mA$	_	1.5	2.5	V	
Switching Time	Turn-on Time	t _{on}	OUTPUT 20 μ s I_{B1} \mathcal{L}	ı	0.5	_		
	Storage Time	${ m t_{stg}}$	I_{B1} I_{B2} I_{B1} I_{B2} I_{B2} I_{B1}	_	5.0	_	μ s	
	Fall Time	t_f	$\begin{bmatrix} I_{B1} = -I_{B2} = 4mA & V_{CC} = 40V \\ DUTY \ CYCLE \leq 1\% \end{bmatrix}$		0.7	_		

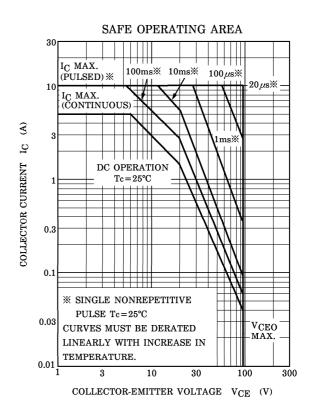












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